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12/6/00

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

File the application of:

SHI-QING WANG, ET AL

Docket: 30-4687 (4780)

Serial Number: 09/328,646

Group Art Unit: 2811

Filed: June 9, 1999

Examiner: H. Vu

For: INTEGRATED CIRCUITS WITH MULTIPLE LOW DIELECTRIC-CONSTANT  
INTER-METAL DIELECTRICS

AMENDMENT

Assistant Commissioner for Patents  
Washington, DC 20231

Sir:

In response to the Office Action mailed October 3, 2000 applicant makes the following  
election in response to the restriction requirement.

In the claims:

- EI
- ~~(Circular stamp with a large X over it)~~
7. (Amended) [A process for producing an] An integrated circuit structure produced by a  
process which comprises
- (a) providing a substrate which comprises a pattern of metal lines on the substrate and a dielectric on the substrate between the metal lines;
  - (b) depositing an organic dielectric layer on the substrate;
  - (c) depositing an inorganic dielectric layer on the organic dielectric;
  - (d) etching a pattern of vias through the inorganic dielectric layer;
  - (e) etching a pattern of vias through the organic dielectric layer which correspond to the pattern of vias through the inorganic dielectric layer;
  - (f) applying a photoresist to the top of the inorganic dielectric layer and filling the vias in the organic dielectric layer and the inorganic dielectric layer with photoresist;

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